

Nell Semiconductors

## Dual Common-Cathode Schottky Rectifier, 60A (30A x2), 45V



### FEATURES

- 150°C  $T_J$  operation
- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness, long term reliability and overvoltage protection
- Compliant to RoHS
- Designed and qualified according to JEDEC-JESD47
- Solder bath temperature 260°C maximum, 40 s per JESD 22B-106 (for TO-247AB package)

### DESCRIPTION

The **MBR6045PT** Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150°C junction temperature.

### APPLICATIONS

- Switching mode power supplies
- DC to DC converters
- Freewheeling diodes
- Reverse battery protection.

### MECHANICAL DATA

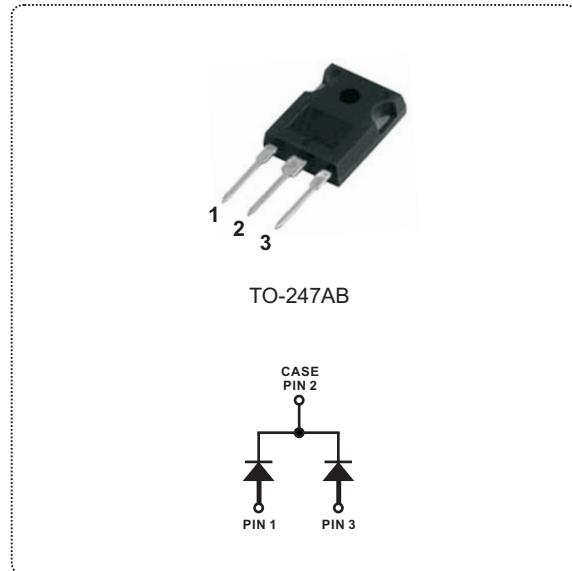
**Case:** TO-247AB (TO-3P)

Molding compound meets UL 94 V-O  
flammability rating

**Terminals:** Mat tin plated leads, solderable per  
J-STD-002 and JESD 22-B102

**Polarity:** As marked

**Mounting Torque:** 10 in-lbs maximum



### PRODUCT SUMMARY

$I_{F(AV)}$	30A x 2
$V_R$	45V
$V_F$ at $I_F$	0.55V
$I_{RM}$ max.	150mA at 125°C
$T_J$ max.	150°C
Diode variation	Dual dice, Common cathode
$E_{AS}$	27 mJ

### MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUE	UNIT
$I_{F(AV)}$	Rectangular waveform	30 x 2	A
$V_{RRM}$		45	V
$I_{FSM}$	8.3 ms single half sine-wave	380	A
$V_F$	$30 A_{pk}$ , $T_J = 125^\circ C$	0.55	V
$T_J$	Range	-65 to 150	°C

**VOLTAGE RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Maximum DC reverse voltage	$V_R$	45	V
Maximum working peak reverse voltage	$V_{RWM}$		
Maximum DC blocking voltage	$V_{DC}$		

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNIT
Maximum average forward current per device per diode	$I_{F(AV)}$	$T_J = 122^\circ C$ , rated $V_R$	60	A
			30	
Non-repetitive peak surge current	$I_{FSM}$	Surge applied at rated load condition half wave single phase 60 Hz	380	A
Non-repetitive avalanche energy	$E_{AS}$	$T_J = 25^\circ C$ , $I_{AS} = 4A$ , $L = 3.4mH$	27	mJ
Repetitive avalanche current	$I_{AR}$	Current decaying linearly to zero in 1 $\mu s$ Frequency limited by $T_J$ maximum $V_A = 1.5 \times V_R$ typical	6	A

**ELECTRICAL SPECIFICATIONS**

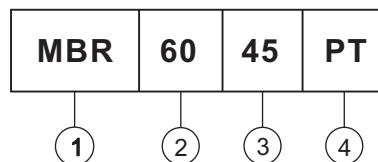
PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNIT
Maximum forward voltage drop	$V_{FM}^{(1)}$	$I_F = 30A$	$T_J = 25^\circ C$	0.62
		$I_F = 60A$		0.75
		$I_F = 30A$	$T_J = 125^\circ C$	0.55
		$I_F = 60A$		0.70
Maximum instantaneous reverse current	$I_{RM}^{(1)}$	$T_J = 25^\circ C$	Rated DC voltage	1
		$T_J = 125^\circ C$		150
Maximum junction capacitance	$C_T$	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) $25^\circ C$	1400	pF
Typical series inductance	$L_S$	Measured from top of terminal to mounting plane	7.5	nH
Maximum voltage rate of change	$dV/dt$	Rated $V_R$	10000	V/ $\mu s$

**Note**

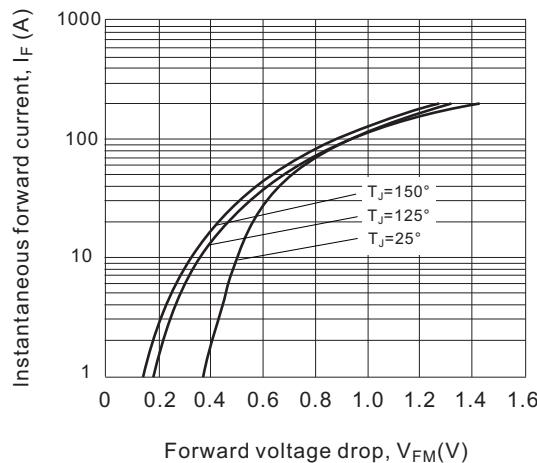
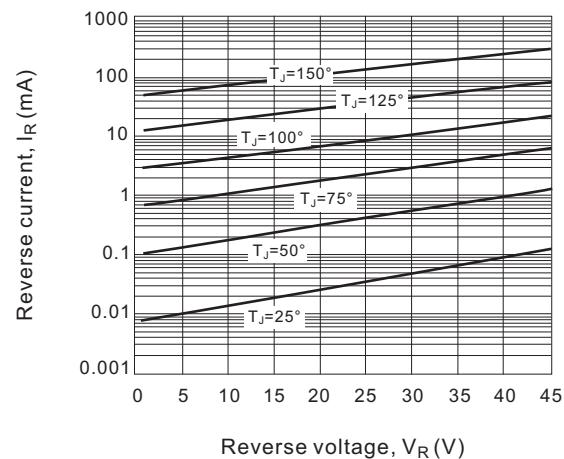
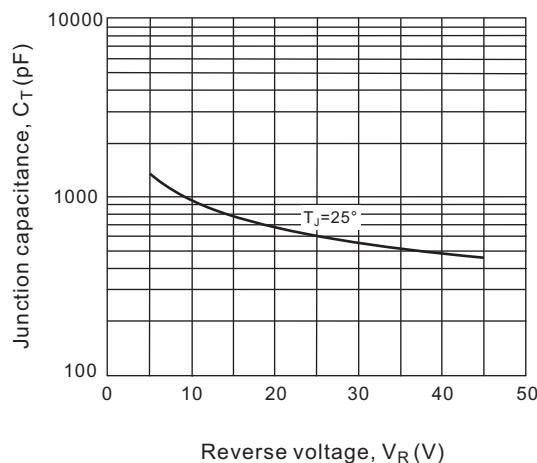
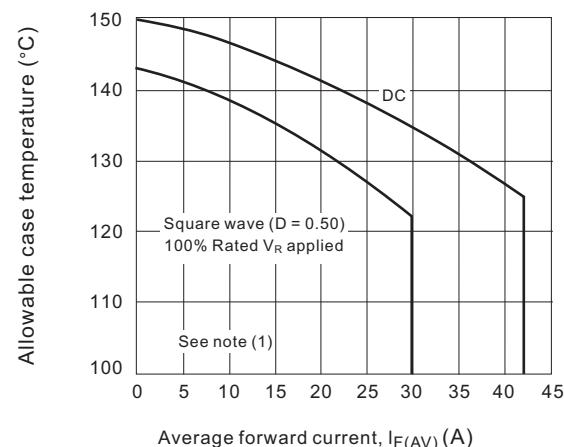
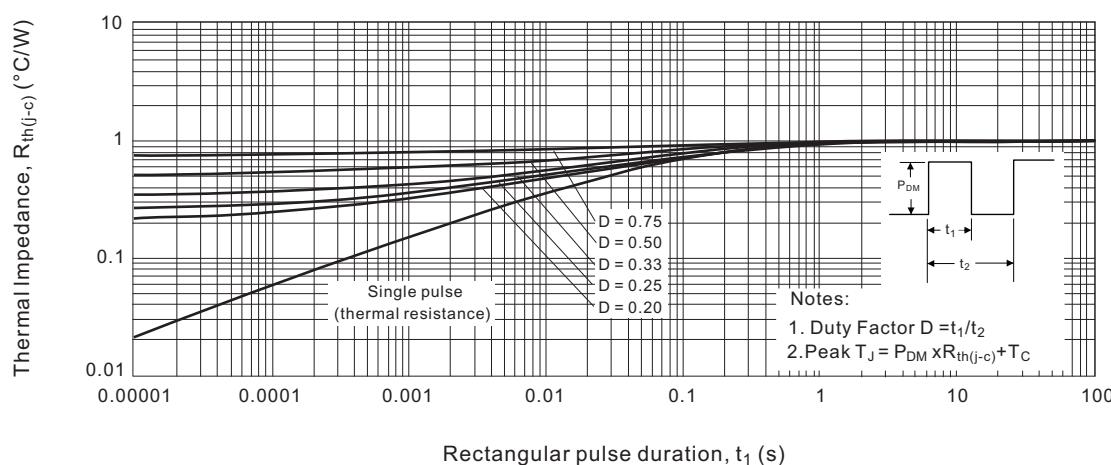
(1) Pulse width < 300  $\mu s$ , duty cycle < 2%

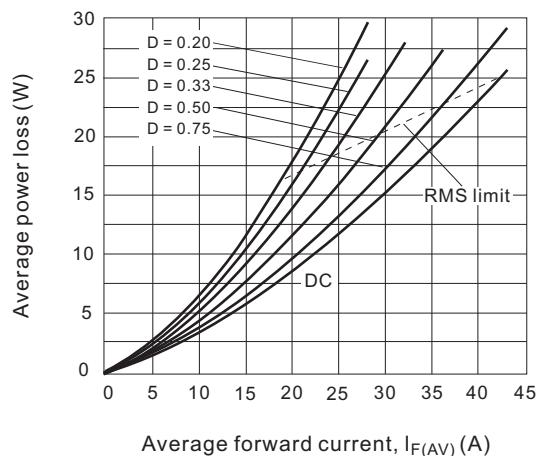
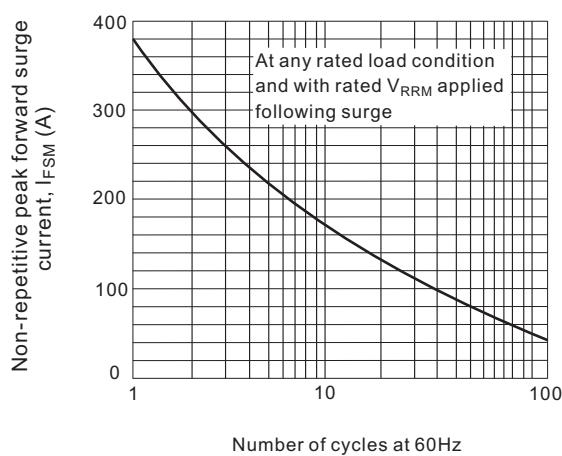
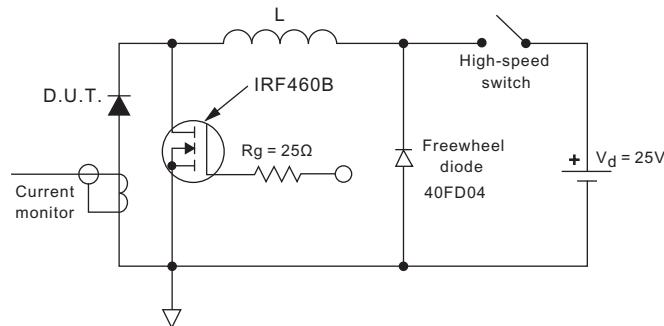
**THERMAL - MECHANICAL SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNIT
Maximum junction temperature range	$T_J$		-65 to 150	$^{\circ}\text{C}$
Maximum storage temperature range	$T_{\text{stg}}$		-65 to 150	
Maximum thermal resistance, junction to case	$R_{\text{thJC}}$	DC operation	1.0	$^{\circ}\text{C/W}$
Typical thermal resistance, case to heatsink	$R_{\text{thCS}}$		0.24	
Approximate weight			6.2	g
			0.22	oz.
Mounting torque	minimum		6 (5)	$\text{kgf} \cdot \text{cm}$ (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-247 AB	MBR6045PT	

**Ordering Information Table**
**Device code**


- [1]** - Schottky MBR series
- [2]** - Current rating (60 = 60A, 30A x 2)
- [3]** - Voltage ratings, 45 = 45V
- [4]** - Circuit configuration, Center tap common cathode,  
TO-247 AB series package

**Fig.1 Maximum forward voltage drop characteristics (Per Leg)**

**Fig.2 Typical values of reverse current vs. reverse voltage (Per Leg)**

**Fig.3 Typical junction capacitance vs. reverse voltage (Per Leg)**

**Fig.4 Maximum allowable case temperature vs. average forward current (Per Leg)**

**Fig.5 Maximum thermal impedance  $R_{th(j-c)}$  characteristics (Per Leg)**


**Fig.6 Forward power loss characteristics  
(Per Leg)**

**Fig.7 Maximum non-repetitive peak worward surge current (Per Leg)**

**Fig.8 Unclamped inductive test circuit**

**Note**

- (1) Formula used:  $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$ ;
- $P_d$  = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig.6);
- $P_{dREV}$  = Inverse power loss =  $V_{R1} \times I_R (1-D)$ ;  $I_R$  at  $V_{R1} = 100\% \text{ Rated } V_R$

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